

IN THE CLAIMS:

1. (Original) A film formation method comprising the steps of:
forming a first film in a chamber by using a first gas;
installing a substrate into the chamber after forming the first film; and
forming a second film over a surface of the substrate by using the first film and a second gas.
2. (Original) A film formation method according to claim 1, wherein the second film is formed at a pressure of 20 Pa or less.
3. (Original) A film formation method according to claim 1, wherein the second film is formed over one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.
4. (Original) A film formation method according to claim 1, wherein the first film is formed by plasma CVD, and the second film is precipitated by sputtering.
5. (Original) A film formation method according to claim 1, wherein a semiconductor device is manufactured by using the second film as a protective film of a semiconductor element.
6. (Previously Presented) A film formation method according to claim 5, wherein the semiconductor element comprises at least one selected from the group consisting of a thin film transistor, an organic thin film transistor, a thin film diode, a photoelectric conversion element, and a resistor.

7. (Original) A film formation method comprising the steps of:
forming a first film in a chamber by using a first gas;
installing a substrate into the chamber after forming the first film; and
forming a silicon nitride film over a surface of the substrate by using the first film and
a second gas.
8. (Original) A film formation method according to claim 7, wherein the first
gas comprises a silicide gas and nitrogen.
9. (Original) A film formation method according to claim 7, wherein the second
gas comprises at least one selected from the group consisting of helium (He), neon (Ne),
argon (Ar), krypton (Kr), and xenon (Xe).
10. (Currently Amended) A film formation method according to claim 7, wherein
~~the second film~~ the silicon nitride film is formed at a pressure of 20 Pa or less.
11. (Original) A film formation method according to claim 7, wherein the second
film is formed over one selected from the group consisting of a glass substrate, a plastic
substrate, and an organic resin film.
12. (Original) A film formation method according to claim 7, wherein the first
film is formed by plasma CVD, and the second film is precipitated by sputtering.
13. (Original) A film formation method according to claim 8, wherein the silicide
gas comprises at least one selected from the group consisting of monosilane, disilane, and
trisilane.
14. (Currently Amended) A film formation method according to claim 7, wherein
a semiconductor device is manufactured by using ~~the second film~~ the silicon nitride film as a
protective film of a semiconductor element.

15. (Previously presented) A film formation method according to claim 4, wherein the semiconductor element comprises at least one selected from the group consisting of a thin film transistor, an organic thin film transistor, a thin film diode, a photoelectric conversion element, and a resistor.

16. (Original) A film formation method comprising the steps of:
forming a first film in a chamber by using a first gas;
installing a substrate into the chamber after forming the first film; and
forming a silicon oxide film over a surface of the substrate by using the first film and a second gas.

17. (Original) A film formation method according to claim 16, wherein the first gas comprises a silicide gas and oxygen.

18. (Original) A film formation method according to claim 16, wherein the second gas comprises at least one selected from the group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

19. (Original) A film formation method according to claim 16, wherein the second film is formed at a pressure of 20 Pa or less.

20. (Original) A film formation method according to claim 16, wherein the second film is formed over one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

21. (Original) A film formation method according to claim 16, wherein the first film is formed by plasma CVD, and the second film is precipitated by sputtering.

22. (Original) A film formation method according to claim 17, wherein the silicide gas comprises at least one selected from the group consisting of monosilane, disilane, and trisilane.

23. (Original) A film formation method according to claim 16, wherein a semiconductor device is manufactured by using the second film as a protective film of a semiconductor element.

24. (Previously Presented) A film formation method according to claim 23, wherein the semiconductor element comprises at least one selected from the group consisting of a thin film transistor, an organic thin film transistor, a thin film diode, a photoelectric conversion element, and a resistor.

25. (Original) A film formation method comprising the steps of:
forming a first film in a chamber by using a first gas;
installing a substrate into the chamber after forming the first film; and
forming a silicon oxynitride film over a surface of the substrate by using the first film and a second gas.

26. (Original) A film formation method according to claim 25, wherein the first gas comprises a silicide gas, oxygen, and nitrogen.

27. (Original) A film formation method according to claim 25, wherein the second gas comprises at least one selected from the group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

28. (Original) A film formation method according to claim 25, wherein the second film is formed at a pressure of 20 Pa or less.

29. (Original) A film formation method according to claim 25, wherein the second film is formed over one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

30. (Original) A film formation method according to claim 25, wherein the first film is formed by plasma CVD, and the second film is precipitated by sputtering.

31. (Original) A film formation method according to claim 26, wherein the silicide gas comprises at least one selected from the group consisting of monosilane, disilane, and trisilane.

32. (Original) A film formation method according to claim 25, wherein a semiconductor device is manufactured by using the second film as a protective film of a semiconductor element.

33. (Previously Presented) A film formation method according to claim 32, wherein the semiconductor element comprises at least one selected from the group consisting of a thin film transistor, an organic thin film transistor, a thin film diode, a photoelectric conversion element, and a resistor.

34. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a thin film transistor over a substrate, wherein the thin film transistor comprises an active region and a gate electrode with a gate insulating film interposed therebetween;

forming a first film in a chamber by using a first gas;
installing the substrate into the chamber after forming the first film; and
forming a second film over the thin film transistor by using the first film and a second gas.

35. (Previously Presented) A method for manufacturing a semiconductor device according to claim 34, wherein the second film is formed at a pressure of 20 Pa or less.

36. (Previously Presented) A method for manufacturing a semiconductor device according to claim 34, wherein the substrate comprises at least one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

37. (Previously Presented) A method for manufacturing a semiconductor device according to claim 34, wherein the first film is formed by plasma CVD, and the second film is precipitated by sputtering.

38. (Previously Presented) A method for manufacturing a semiconductor device according to claim 34, further comprising a step of forming an EL layer and an electrode over the second film.

39. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a thin film transistor over a substrate, wherein the thin film transistor comprises an active region and a gate electrode with a gate insulating film interposed therebetween;

forming a first film in a chamber by using a first gas;

installing the substrate into the chamber after forming the first film; and

forming a silicon nitride film over the thin film transistor by using the first film and a second gas.

40. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the first gas comprises a silicide gas and nitrogen.

41. (Previously Presented) A method for manufacturing a semiconductor device according to claim 40, wherein the silicide gas comprises at least one selected from the group consisting of monosilane, disilane, and trisilane.

42. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the second gas comprises at least one selected from the group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

43. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the second film is formed at a pressure of 20 Pa or less.

44. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the substrate comprises at least one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

45. (Previously Presented) A film formation method according to claim 39, wherein the first film is formed by plasma CVD, and the second film is precipitated by sputtering.

46. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, further comprising a step of forming an EL layer and an electrode over the second film.

47. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a thin film transistor over a substrate, wherein the thin film transistor comprises an active region and a gate electrode with a gate insulating film interposed therebetween;

forming a first film in a chamber by using a first gas;

installing the substrate into the chamber after forming the first film; and

forming a silicon oxide film over the thin film transistor by using the first film and a second gas.

48. (Previously Presented) A method for manufacturing a semiconductor device according to claim 47, wherein the first gas comprises a silicide gas and nitrogen.

49. (Previously Presented) A method for manufacturing a semiconductor device according to claim 48, wherein the silicide gas comprises at least one selected from the group consisting of monosilane, disilane, and trisilane.

50. (Previously Presented) A method for manufacturing a semiconductor device according to claim 47, wherein the second gas comprises at least one selected from the group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

51. (Previously Presented) A method for manufacturing a semiconductor device according to claim 47, wherein the second film is formed at a pressure of 20 Pa or less.

52. (Previously Presented) A method for manufacturing a semiconductor device according to claim 47, wherein the substrate comprises at least one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

53. (Previously Presented) A film formation method according to claim 47, wherein the first film is formed by plasma CVD, and the second film is precipitated by sputtering.

54. (Previously Presented) A method for manufacturing a semiconductor device according to claim 47, further comprising a step of forming an EL layer and an electrode over the second film.

55. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a thin film transistor over a substrate, wherein the thin film transistor comprises an active region and a gate electrode with a gate insulating film interposed therebetween;

forming a first film in a chamber by using a first gas;

installing the substrate into the chamber after forming the first film; and

forming a silicon oxynitride film over the thin film transistor by using the first film and a second gas.

56. (Previously Presented) A method for manufacturing a semiconductor device according to claim 55, wherein the first gas comprises a silicide gas and nitrogen.

57. (Previously Presented) A method for manufacturing a semiconductor device according to claim 56, wherein the silicide gas comprises at least one selected from the group consisting of monosilane, disilane, and trisilane.

58. (Previously Presented) A method for manufacturing a semiconductor device according to claim 55, wherein the second gas comprises at least one selected from the group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

59. (Previously Presented) A method for manufacturing a semiconductor device according to claim 55, wherein the second film is formed at a pressure of 20 Pa or less.

60. (Previously Presented) A method for manufacturing a semiconductor device according to claim 55, wherein the substrate comprises at least one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

61. (Previously Presented) A film formation method according to claim 55, wherein the first film is formed by plasma CVD, and the second film is precipitated by sputtering.

62. (Previously Presented) A method for manufacturing a semiconductor device according to claim 55, further comprising a step of forming an EL layer and an electrode over the second film.

63. (New) A film formation method comprising the steps of:
forming a first film on internal portions of a chamber by using a first gas;
installing a substrate into the chamber after forming the first film; and
forming a silicon nitride film over a surface of the substrate by using the first film and a second gas.

64. (New) A film formation method according to claim 63, wherein the first gas comprises a silicide gas and nitrogen.

65. (New) A film formation method according to claim 63, wherein the second gas comprises at least one selected from the group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

66. (New) A film formation method according to claim 63, wherein the silicon nitride film is formed at a pressure of 20 Pa or less.

67. (New) A film formation method according to claim 63, wherein the silicon nitride film is formed over one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

68. (New) A film formation method according to claim 63, wherein the first film is formed by plasma CVD, and the silicon nitride film is precipitated by sputtering.

69. (New) A film formation method according to claim 64, wherein the silicide gas comprises at least one selected from the group consisting of monosilane, disilane, and trisilane.

70. (New) A film formation method according to claim 63, wherein a semiconductor device is manufactured by using the silicon nitride film as a protective film of a semiconductor element.

71. (New) A film formation method according to claim 70, wherein the semiconductor element comprises at least one selected from the group consisting of a thin film transistor, an organic thin film transistor, a thin film diode, a photoelectric conversion element, and a resistor.

72. (New) A method for manufacturing a semiconductor device comprising:
forming a thin film transistor over a substrate, wherein the thin film transistor comprises an active region and a gate electrode with a gate insulating film interposed therebetween;
forming a first film on internal portions of a chamber by using a first gas;
installing the substrate into the chamber after forming the first film; and
forming a second film over the thin film transistor by using the first film and a second gas.

73. (New) A method for manufacturing a semiconductor device according to claim 72, wherein the first gas comprises a silicide gas and nitrogen.

74. (New) A method for manufacturing a semiconductor device according to claim 72, wherein the second gas comprises at least one selected from the group consisting of helium (He), neon (Ne), argon (Ar), krypton (Kr), and xenon (Xe).

75. (New) A method for manufacturing a semiconductor device according to claim 72, wherein the second film is formed at a pressure of 20 Pa or less.

76. (New) A method for manufacturing a semiconductor device according to claim 72, wherein the second film is formed over one selected from the group consisting of a glass substrate, a plastic substrate, and an organic resin film.

77. (New) A method for manufacturing a semiconductor device according to claim 72, wherein the first film is formed by plasma CVD, and the second film is precipitated by sputtering.

78. (New) A method for manufacturing a semiconductor device according to claim 73, wherein the silicide gas comprises at least one selected from the group consisting of monosilane, disilane, and trisilane.

79. (New) A method for manufacturing a semiconductor device according to claim 72, further comprising a step of forming an EL layer and an electrode over the second film.